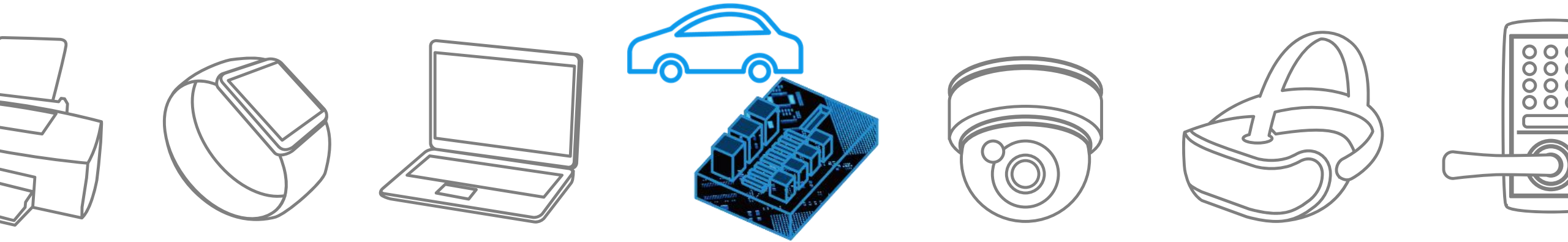


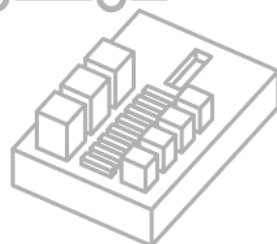
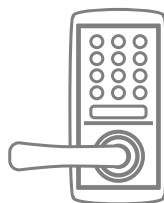
TOSHIBA

Automotive Junction Box

Solution Proposal by Toshiba

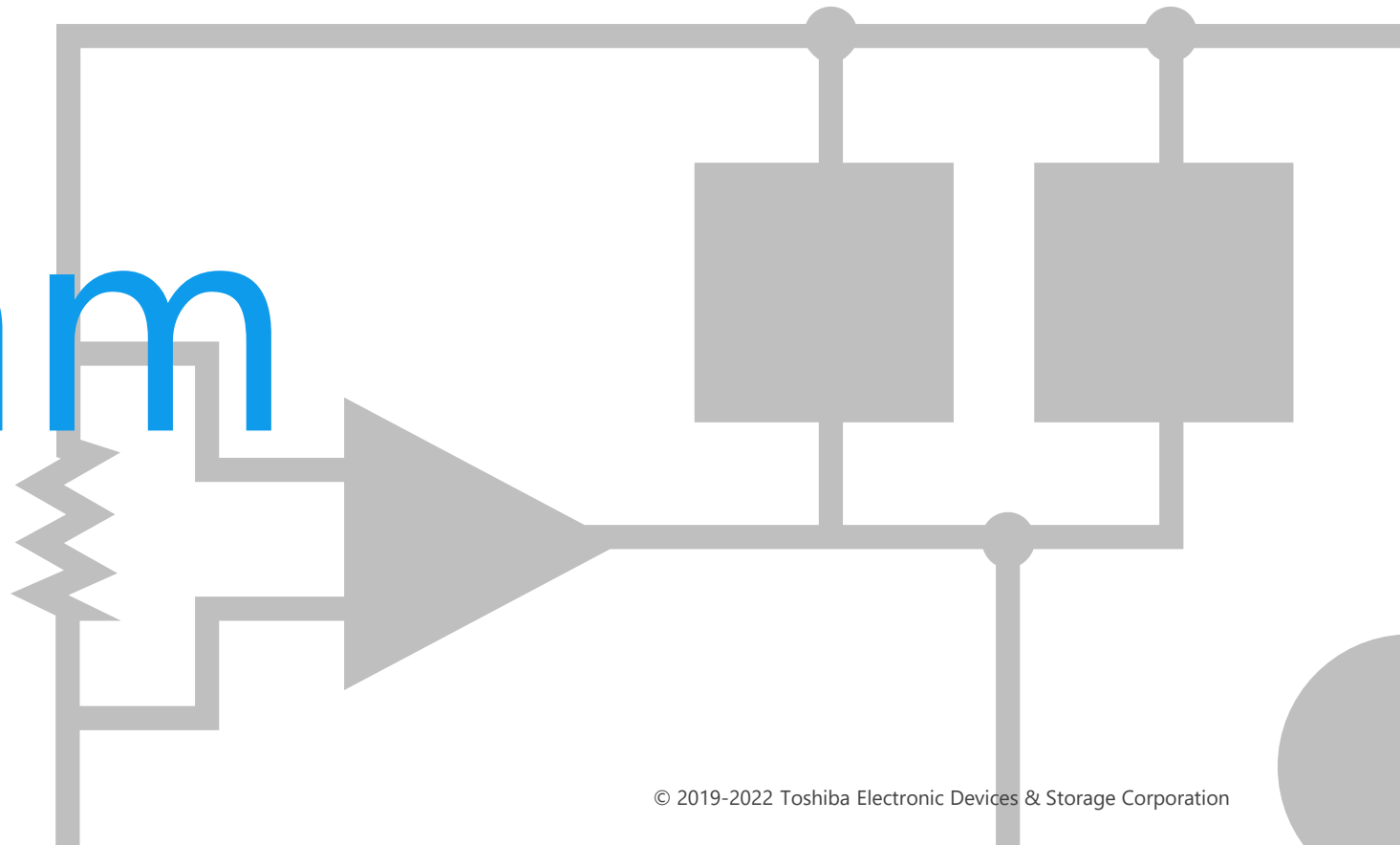
R21



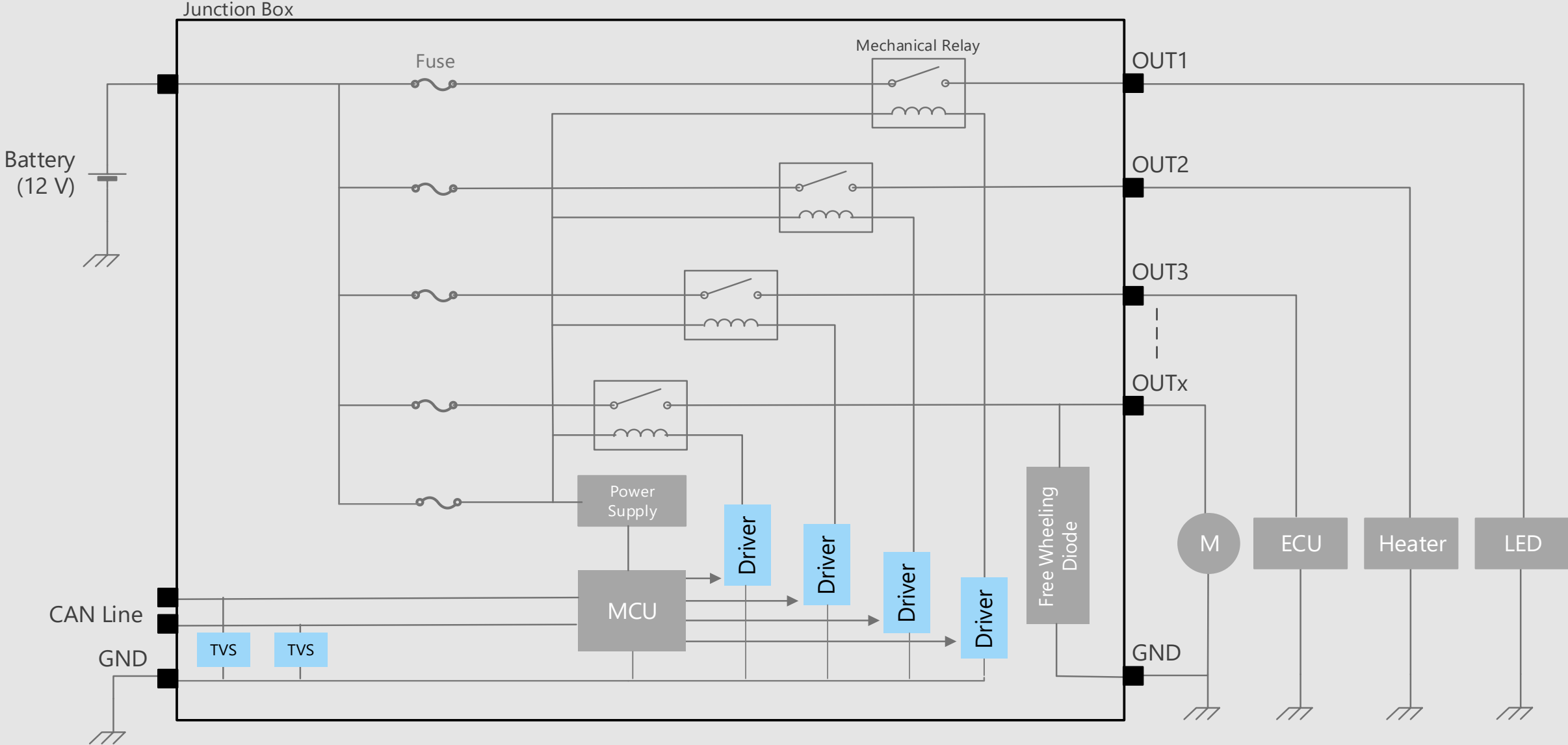


Toshiba Electronic Devices & Storage Corporation provides comprehensive device solutions to customers developing new products by applying its thorough understanding of the systems acquired through the analysis of basic product designs.

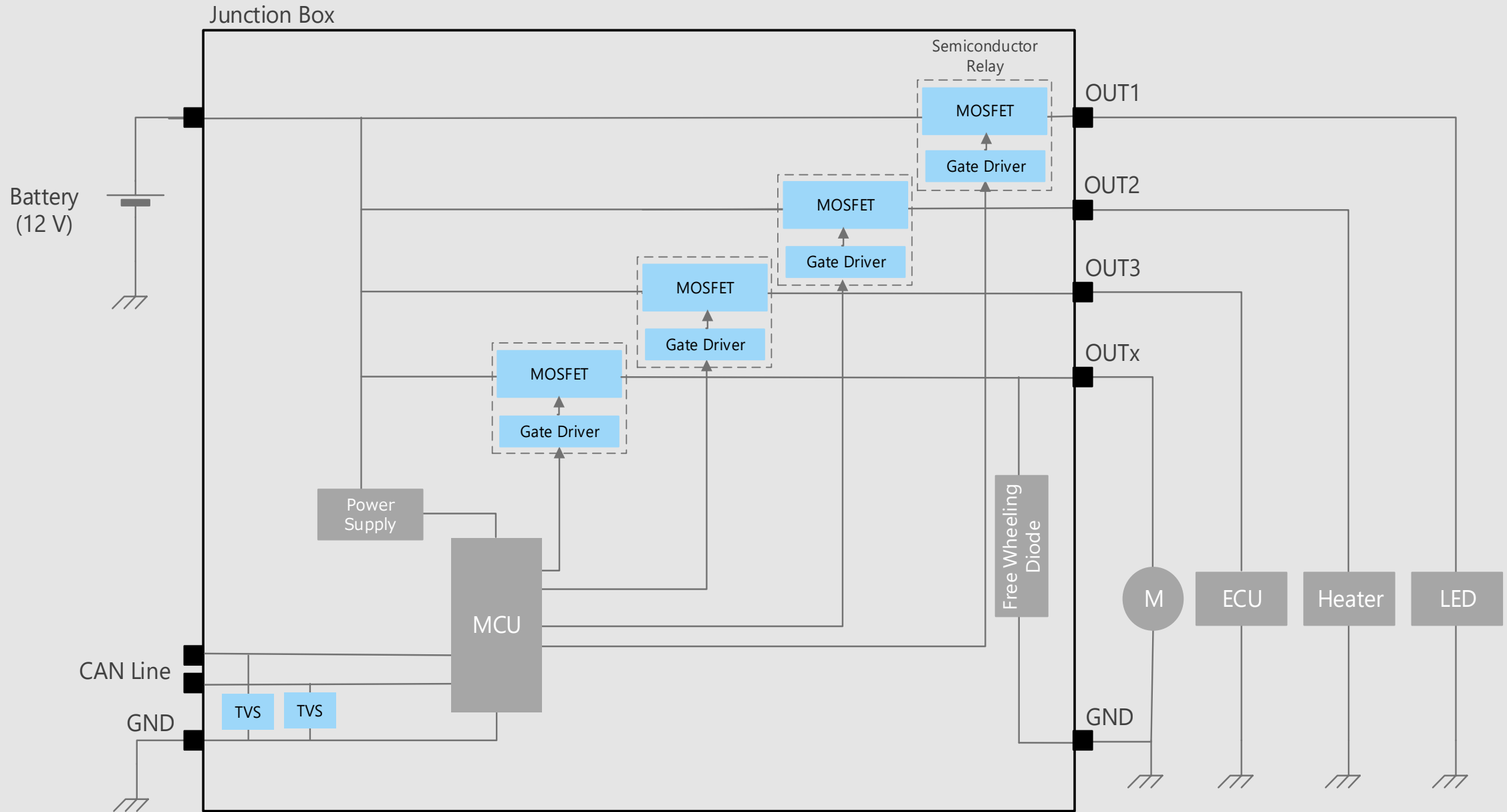
Block Diagram



Junction Box Overall block diagram (Mechanical relay system)

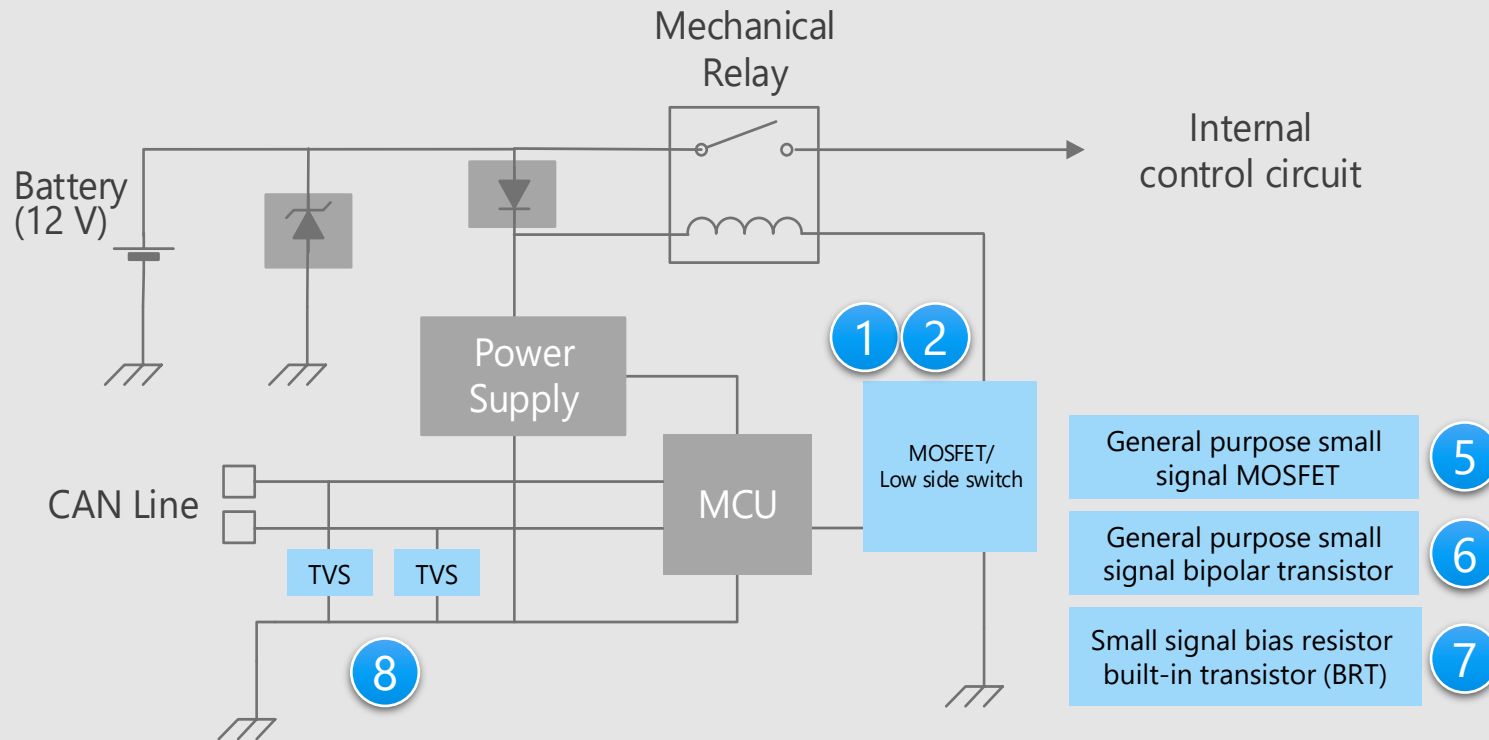


Junction Box Overall block diagram (Semiconductor relay system)



Junction Box Detail of mechanical relay system

Mechanical relay system



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

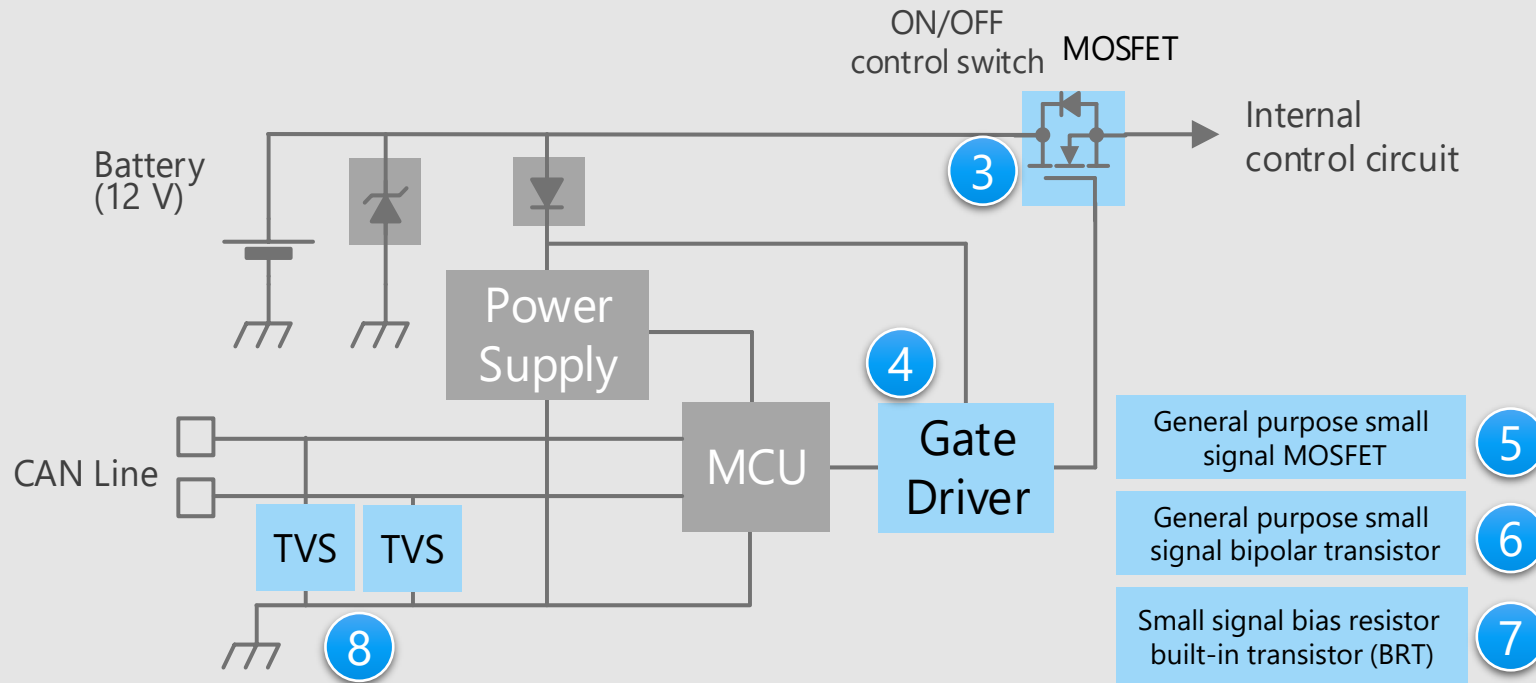
- It is necessary to select a device that can protect the system from the voltage generated by the back electromotive force (EMF) of inductive loads.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

- **Built-in active clamp circuit and pull-down resistor for relay drive**
 - 1: MOSFET with a built-in active clamp circuit
 - 2: Low side switch / high side switch (up to 1 A)
- **Driver with protection function**
 - 5: General purpose small signal MOSFET
 - 6: General purpose small signal bipolar transistor
 - 7: Small signal bias resistor built-in transistor (BRT)
- **Suitable for ESD protection**
 - 8: TVS diode (for CAN communication)

Junction Box Detail of semiconductor relay system

Semiconductor relay system



Criteria for device selection

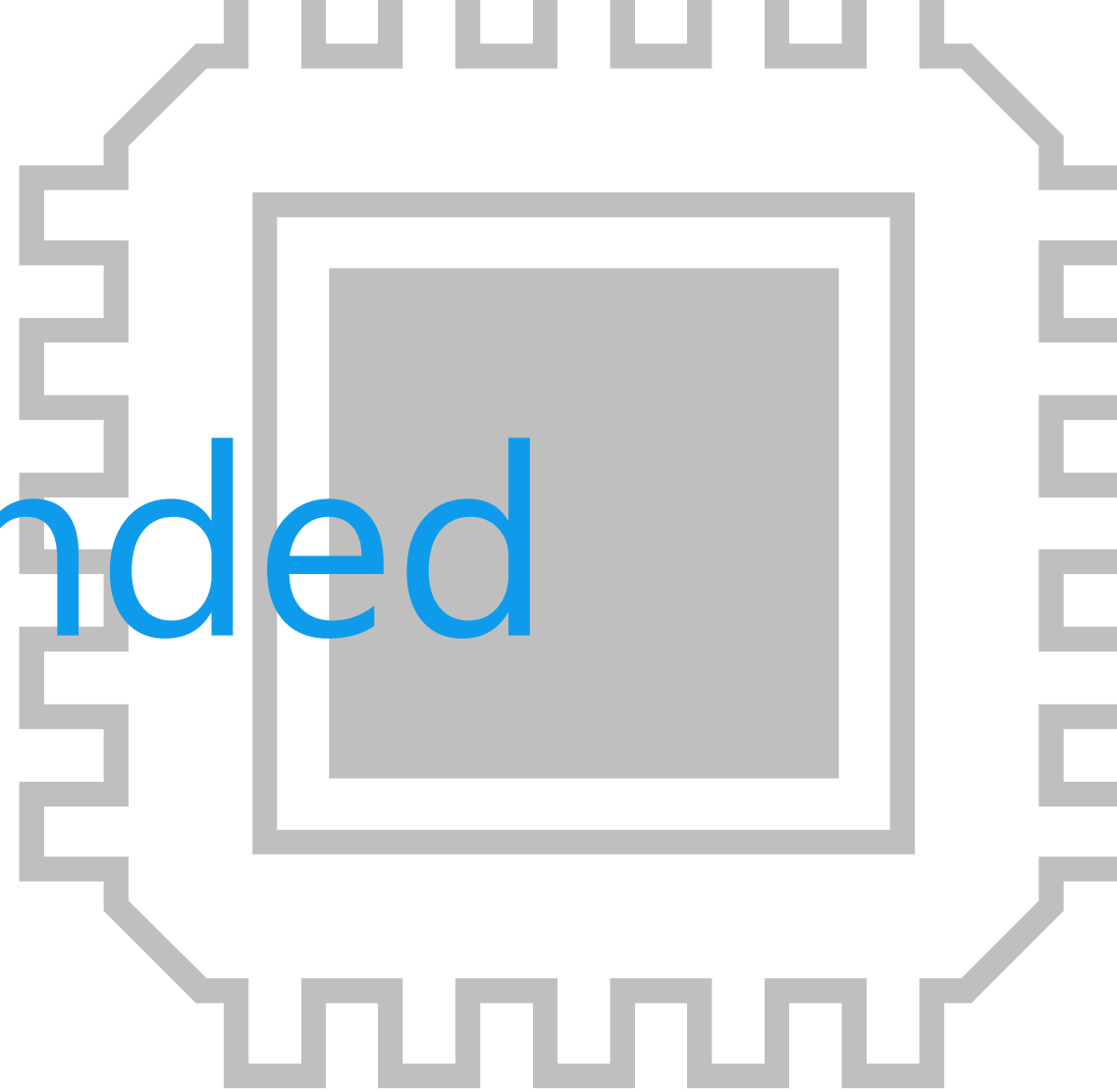
- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

- **Low on-resistance contributes to low power consumption of the system**
U-MOS Series 40 V N-ch MOSFET
- **Gate driver with built-in protection and diagnosis functions**
Gate driver (for switch)
- **Extensive product lineup**
General purpose small signal MOSFET
General purpose small signal bipolar transistor
Small signal bias resistor built-in transistor (BRT)
- **Suitable for ESD protection**
TVS diode (for CAN communication)

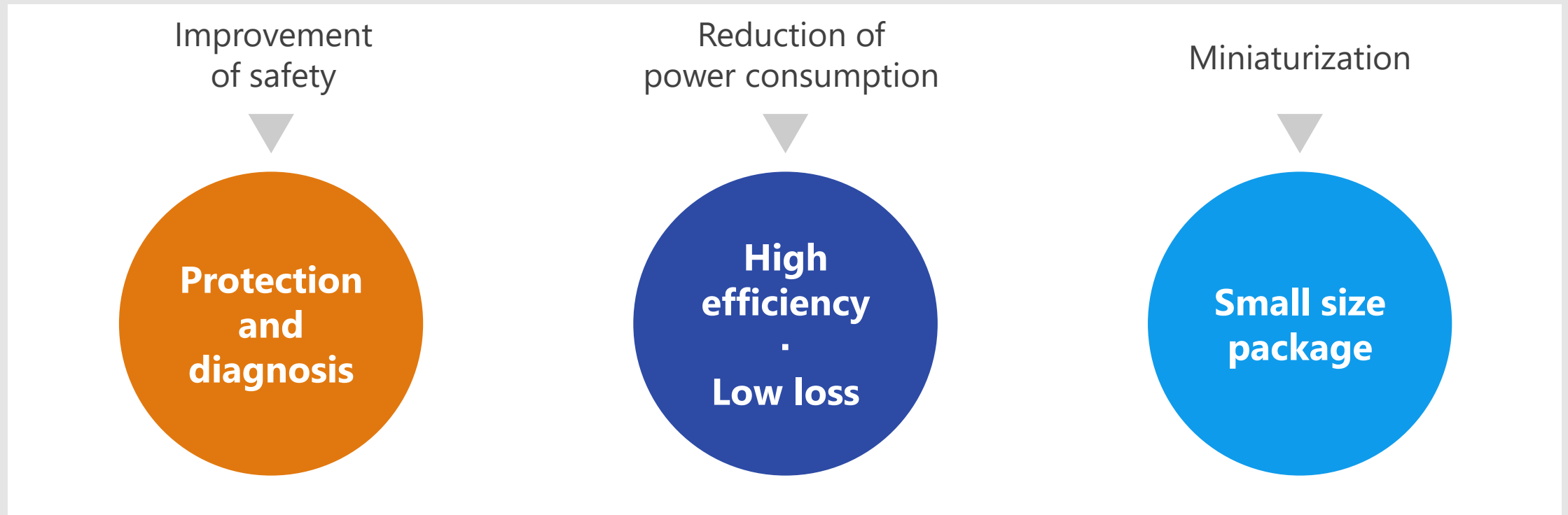
* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Recommended Devices



Device solutions to address customer needs

As described above, in the design of Junction Box, **“Improvement of safety”**, **“Reduction of power consumption”** and **“Miniaturization”** are important factors. Toshiba’s proposals are based on these three solution perspectives.



Device solutions to address customer needs



	Protection and diagnosis	High efficiency Low loss	Small size package
1 MOSFET with a built-in active clamp circuit	●	●	●
2 Low side switch / High side switch (up to 1 A)	●		●
3 U-MOS Series 40 V N-ch MOSFET		●	●
4 Gate driver (for switch)	●		●
5 General purpose small signal MOSFET		●	●
6 General purpose small signal bipolar transistor			●
7 Small signal bias resistor built-in transistor (BRT)			●
8 TVS diode (for CAN communication)	●		●

Value provided

These devices have a built-in active clamp circuit to reduce the number of components and to save mounting area.

1 Built-in active clamp circuit

MOSFET with a built-in active clamp circuit which connected a zener diode between the drain and gate terminals prevents damage caused by voltage surges generated by inductive loads such as a mechanical relay.

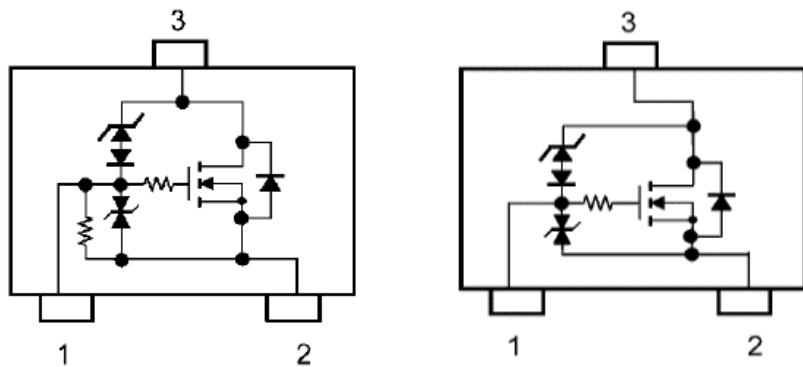
2 Built-in pull-down resistor

SSM3K347R has built-in 47 kΩ pull-down resistor between the gate and source terminals, thus contributes to reduction of number of components and mounting area.

3 Low voltage drive

These devices can be driven at low gate-source voltage of 4.0 V.


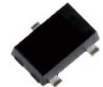
Internal circuit



Pin Assignment

1. Gate
2. Source
3. Drain

Lineup

Part number	SSM3K347R	SSM3K337R
Package	SOT-23F 	SOT-23F 
$V_{DS(DC)}$ [V]	38	38
I_D [A]	2	2
$R_{DS(ON)}$ [mΩ] @ $V_{GS} = 4.0$ V	Typ.	161
	Max	200
Polarity	N-ch	N-ch

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2 Low side switch / High side switch (up to 1 A)

TPD1044F / TPD1054F / TPD1052F

Protection and diagnosis

High efficiency
Low loss

Small size package

Value provided

Various protection and diagnostic output functions are built in, contributing to improve reliability and to miniaturize the system.

1 Built-in various protection and diagnostic output functions

Overcurrent and overheat protection and diagnostic output (except TPD1044F) to the MCUs or the control circuits are built in. These functions contribute to improve reliability of the system.

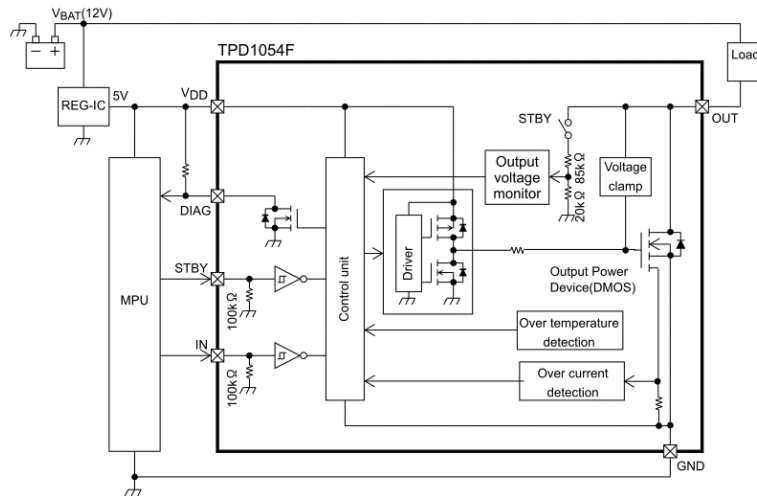
2 Can be controlled by logic level voltage

It is possible to be controlled directly by output signal of MCUs or CMOS logic ICs.


3 Small package

PS-8 is small surface mount package. It contributes to the miniaturization of system.

Example of low side switch application
(Block diagram of TPD1054F)



Suitable for applications with small current load below 1 A, such as mechanical relay

Lineup			
Function	Low side switch		High side switch
Part number	TPD1044F	TPD1054F	TPD1052F
Package	 PS-8 (2.8 x 2.9 mm)		
Features	<ul style="list-style-type: none"> Overcurrent / over-temperature protection Active clamp On-resistance: 0.6 Ω 	<ul style="list-style-type: none"> Overcurrent / over-temperature protection Active clamp Diagnostic output function On-resistance: 0.8 Ω 	<ul style="list-style-type: none"> Overcurrent / over-temperature protection Diagnostic output function On-resistance: 0.8 Ω

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Value provided

The latest processes enables low on-resistance and low noise, thereby reducing power consumption.

1 Low loss (reduced on-resistance)

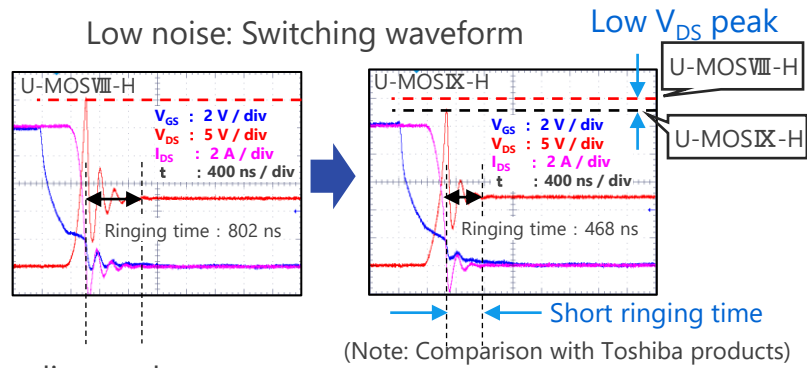
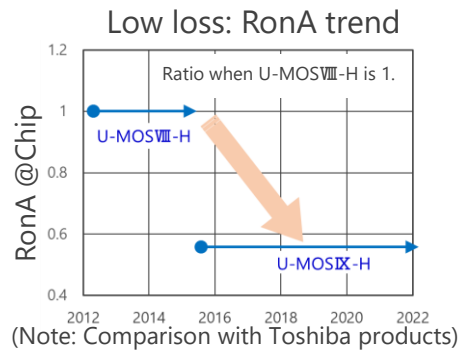
Using low on-resistance technology to contribute to reduced power consumption systems.
On-resistance of 44 % reduction per unit area. (compared to Toshiba's U-MOS[®] VIII-H products)

2 Small and low loss package

By adopting a Cu clip structure and a double-sided heat dissipation structure, low loss and high heat dissipation are realized.
Wettable Flank (WF) package contributes to good mountability.

3 Low noise (low EMI)

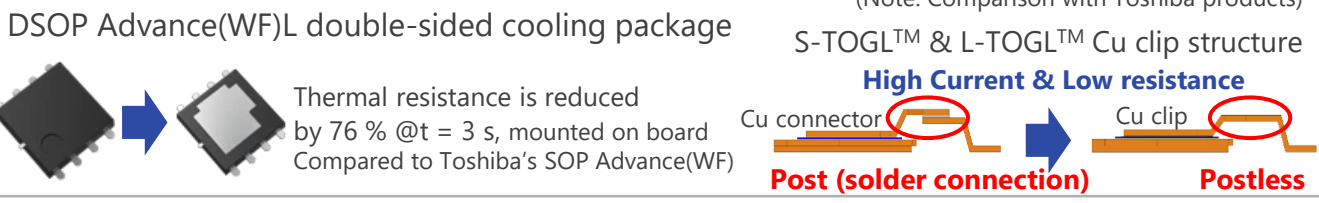
Improved chip process reduces surge voltage and ringing time.



Lineup				
Part number	Rated drain current [A]	On-resistance (Max) [mΩ] @ $V_{GS} = 10 V$	Package	
XPN3R804NC	40	3.8	TSON Advance(WF)	
TK1R4S04PB	120	1.35	DPAK+	
XPHR7904PS	150	0.79	SOP Advance(WF)	
TPWR7904PB	150	0.79	DSOP Advance(WF)L	
XPJR6604PB*	(200)	(0.66)	S-TOGL [™]	
XPQR3004PB	400	0.30	L-TOGL [™]	

* : Under development (Values enclosed in parentheses are tentative specifications. Specifications are subject to change without notice.)

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4 Gate driver (for switch)

TPD7104AF / TPD7106F / TPD7107F

Protection and diagnosis

High efficiency
Low loss

Small size package

Value provided

A charge pump circuit for the N-ch MOSFET gate drive is built in, allowing for easy semiconductor relay configuration.

1 Built-in charge pump circuit

Built-in charge pump circuit enables N-ch MOSFET as high side switch.
Easy to configure a semiconductor relay.

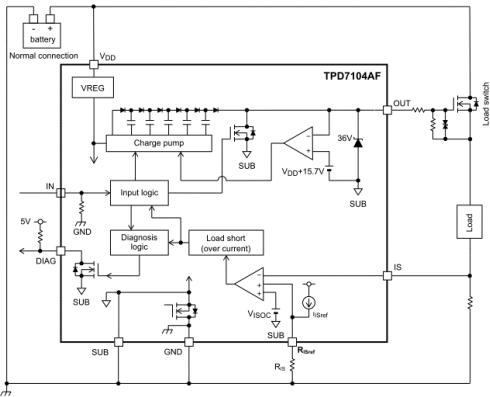
2 Can be controlled by logic level voltage

It is possible to be controlled directly by output signal of MCUs or CMOS logic ICs.

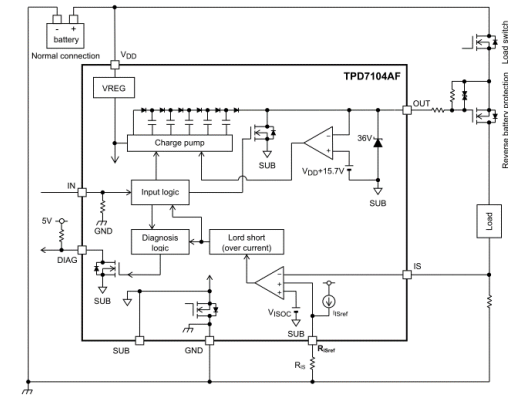
3 Small package

The small surface mount packages such as PS-8, SSOP16 and WSON10A contribute to the miniaturization of equipment.

Semiconductor relay (switch) application (TPD7104AF)






Power supply reverse connection protection MOSFET control (TPD7104AF)



Back to back configuration

Lineup

Part number	TPD7104AF	TPD7106F	TPD7107F
Package	PS-8 (2.8 x 2.9 mm) 	SSOP16 (5.5 x 6.4 mm) 	WSON10A (3 x 3 mm) 
Function	High side gate driver	High side gate driver	High side gate driver
Output	1	1	1
Features	<ul style="list-style-type: none"> Operating power supply voltage range: 5 to 18 V Built-in power supply reverse connection protection function (Protective MOSFET control with back-to-back circuitry) 	<ul style="list-style-type: none"> Operating power supply voltage range: 4.5 to 27 V Built-in power supply reverse connection protection function (Protective MOSFET control with back-to-back circuitry) 	<ul style="list-style-type: none"> Operating power supply voltage range: 5.75 to 26 V Current sense output Protective functions; overcurrent, overtemperature, GND disconnect, etc. reverse battery connection Diagnosis output; overcurrent, load open, overtemperature, etc.

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5 General purpose small signal MOSFET

SSM3K7002KF / SSM3J168F / SSM3J66MFV

Protection
and
diagnosis

High
efficiency
·
Low loss

Small size
package

Value provided

Wide lineup of small packages contribute to reduce the size and power consumption of system.

1 Small package

A lineup of various small packages such as SOT-723 (VESM 1.2 x 1.2 mm package) is available, contributing to reduce mounting area.

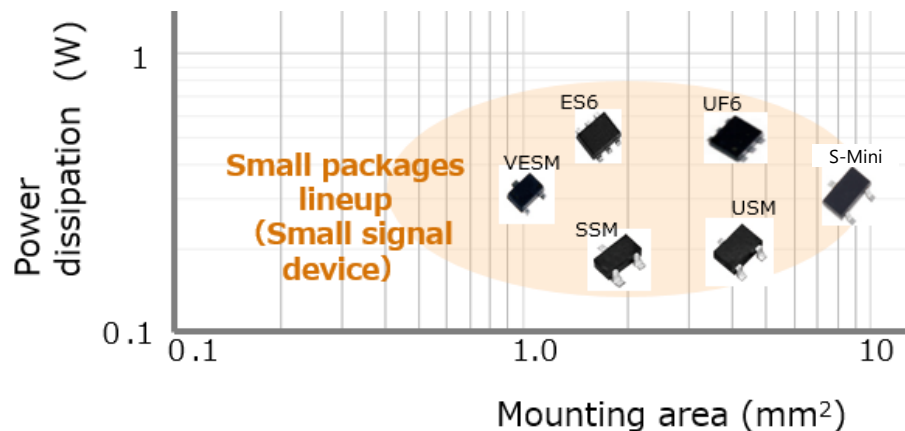
2 Low voltage drive

SSM3J66MFV can be driven at low gate-source voltage of 1.2 V.




3 AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.

Small signal package lineup



Lineup

Part number	SSM3K7002KF	SSM3J168F	SSM3J66MFV
Package	S-Mini (SOT-346) 	S-Mini (SOT-346) 	VESM (SOT-723) 
V_{DSS} [V]	60	-60	-20
I_D [A]	0.4	-0.4	-0.8
$R_{DS(ON)}$ @ $ V_{GS} = 4.5$ V [Ω]	Typ.	1.2	1.4
	Max	1.75	1.9
Drive voltage [V]	4.5	-4.0	-1.2
Polarity	N-ch	P-ch	P-ch

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Value provided

Extensive product lineup to meet customers' needs.

1 Extensive lineup of packages

Various packages such as 1-in-1, 2-in-1 are provided and suitable products for circuit board design are selectable.

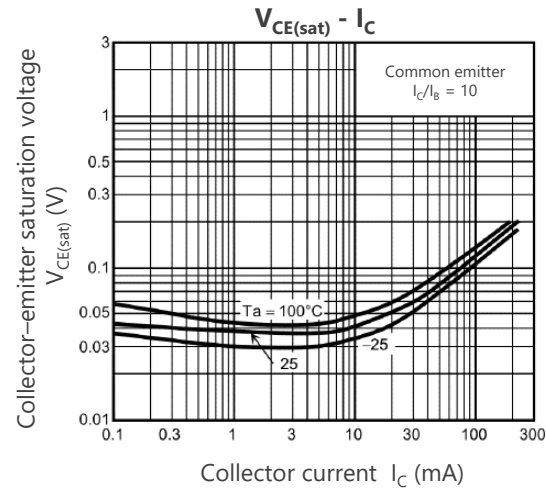
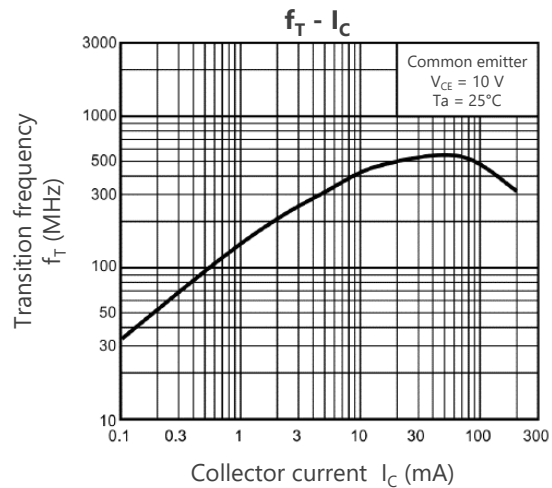
2 Extensive product lineup

Various product lineups, such as general purpose, low noise, low $V_{CE(sat)}$ and high current types are provided. Products can be selected in accordance with the application.

3 AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.

Characteristic examples of 2SC2712



Lineup

Package			SOT-23F		USM (SOT-323) UFM (SOT-323F)*		S-Mini (SOT-346)	
Classification	V_{CE0} [V]	I_C [mA]	NPN	PNP	NPN	PNP	NPN	PNP
General purpose	50	150			2SC4116	2SA1586	2SC2712	2SA1162
	50	500					2SC3325	2SA1313
Low noise	120	100			2SC4117	2SA1587	2SC2713	2SA1163
High current	50	1700				2SA2195*		
	50	2000		TTA501				
	50	2500	TTC501					

* indicates UFM package

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Value provided

Extensive product lineup to meet customers' needs.

1 Built-in bias resistor type (BRT : Bias Resistor built-in Transistor)

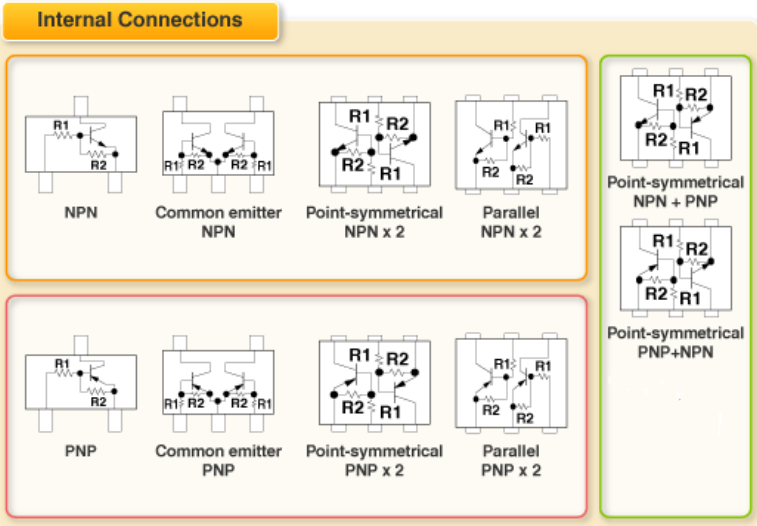
The BRTs contribute to reduction of the number of components, assembly workload and mounting area of circuit boards.

2 Extensive lineup of package and pin assignment

Various package lineups, such as 1-in-1, 2-in-1 and various pin assignment type are provided and suitable products for circuit board design are selectable.

3 AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Lineup			
Part number		NPN (BRT)	PNP (BRT)
Package	ES6 (SOT-563)	RN1907FE	RN2907FE
	US6 (SOT-363)	RN1901	RN2901
V_{CE0} [V]		50	-50
I_C [mA]		100	-100

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8 TVS diode (for CAN communication)

DF3D18FU / DF3D29FU / DF3D36FU

Protection and diagnosis

High efficiency
Low loss

Small size package

Value provided

TVS diodes prevent system damage and malfunction caused by electrostatic discharge (ESD).

1 Improve ESD pulse absorbability

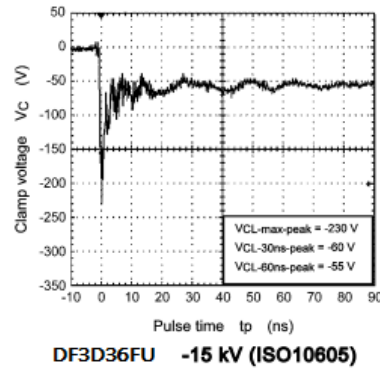
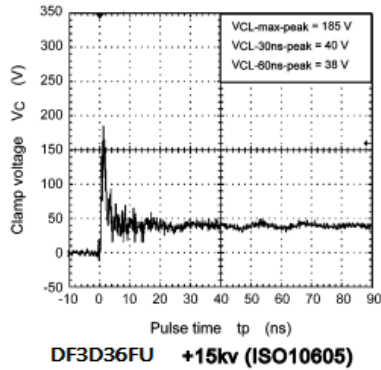
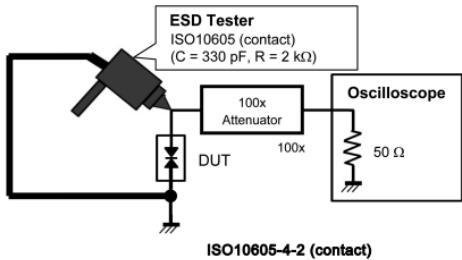
Toshiba proprietary Zener process improves the ESD pulse absorption of TVS diodes.
(Achieving both low dynamic resistance R_{DYN} and low capacitance between terminals C_t)


2 Supports CAN, CAN FD and FlexRay

These are products applicable to in-vehicle LAN communication such as CAN, CAN FD and FlexRay.

3 High ESD immunity

$V_{ESD} > \pm 30$ kV @ ISO 10605
 $V_{ESD} > \pm 20$ kV @ IEC 61000-4-2 (Level 4)



Lineup			
Part number	DF3D18FU	DF3D29FU	DF3D36FU
Package	USM (SOT-323) 		
V_{ESD} [kV] @ISO 10605	± 30	± 30	± 20
V_{RWM} (Max) [V]	12	24	28
C_t (Typ. / Max) [pF]	9 / 10		6.5 / 8
R_{DYN} (Typ.) [Ω]	0.8	1.1	1.5

(Note) The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.
This product is an ESD protection diode and cannot be used for purposes other than ESD protection.

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